# 2SK0601 (2SK601)

# Silicon N-channel MOSFET

### For switching circuits

### ■ Features

- Low drain-souce ON resistance R<sub>DS(on)</sub>
- High-speed switching
- Allowing to be driven directly by CMOS and TTL
- Mini-power type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Drain-source voltage	$V_{DS}$	80	V
Gate-source voltage (Drain open)	$V_{GSO}$	20	V
Drain current	$I_{\mathrm{D}}$	0.5	A
Peak drain current	$I_{DP}$	1.0	A
Power dissipation *	$P_{\mathrm{D}}$	1	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Note) \*: PC board: Copper foil of the drain portion should have a area of 1 cm<sup>2</sup> or more and the board thickness should be 1.7 mm.

# Unit: mm 4.5±0.1 1.6±0.2 1.5±0.1 0.4±0.04 1.5±0.1 1

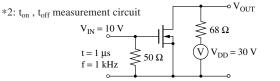
Marking Symbol: Q

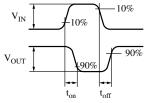
## ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V <sub>DSS</sub>	$I_{DS} = 100  \mu A,  V_{GS} = 0$	80			V
Drain-source cutoff current	I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, V_{GS} = 0$			10	μΑ
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = 20 \text{ V}, V_{DS} = 0$			0.1	μΑ
Gate threshold voltage	$V_{th}$	$I_D = 1 \text{ mA}, V_{DS} = V_{GS}$	1.5		3.5	V
Drain-source ON resistance *1	R <sub>DS(on)</sub>	$I_{\rm D} = 0.5 \text{ A. V}_{\rm GS} = 10 \text{ V}$		2	4	Ω
Forward transfer admittance	$ Y_{fs} $	$I_D = 0.2 \text{ A}, V_{DS} = 15 \text{ V}, f = 1 \text{ kHz}$		300		mS
Short-circuit forward transfer capacitance (Common source)	C <sub>iss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0, \text{ f} = 1 \text{ MHz}$		45		pF
Short-circuit output capacitance (Common source)	Coss			30		pF
Reverse transfer capacitance (Common source)	CC <sub>rss</sub>			8		pF
Turn-on time *2	t <sub>on</sub>			15		ns
Turn-off time *2	t <sub>off</sub>			20		ns

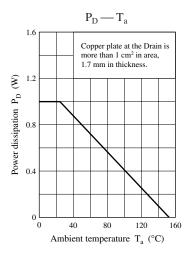
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

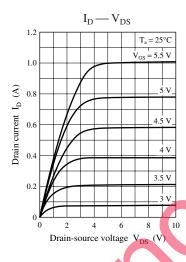
### 2. \*1: Pulse measurement

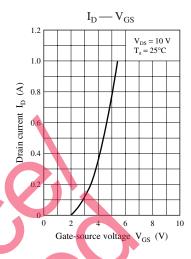


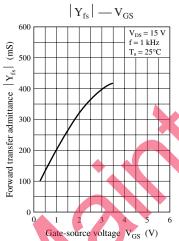


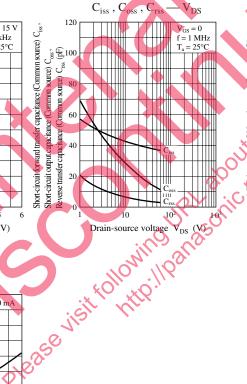
Note) The part number in the parenthesis shows conventional part number.

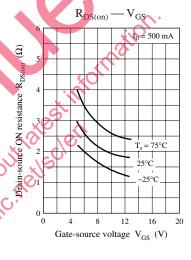


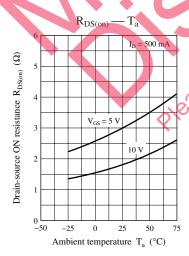












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